

# Silicon PNP Planar RF Transistor

Electrostatic sensitive device.  
Observe precautions for handling.

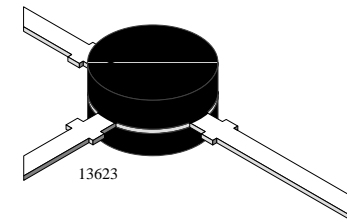
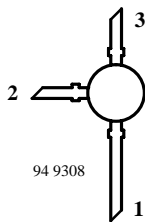


## Applications

UHF oscillator and mixer stages.

## Features

- High gain
- Low noise



BF970 Marking: BF970

Plastic case (TO 50)

1 = Collector, 2 = Base, 3 = Emitter

## Absolute Maximum Ratings

$T_{amb} = 25^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test Conditions	Symbol	Value	Unit
Collector-base voltage		$-V_{CB0}$	40	V
Collector-emitter voltage		$-V_{CEO}$	35	V
Emitter-base voltage		$-V_{EBO}$	3	V
Collector current		$-I_C$	30	mA
Total power dissipation	$T_{amb} \leq 60^{\circ}\text{C}$	$P_{tot}$	300	mW
Junction temperature		$T_j$	150	$^{\circ}\text{C}$
Storage temperature range		$T_{stg}$	-55 to +150	$^{\circ}\text{C}$

## Maximum Thermal Resistance

$T_{amb} = 25^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test Conditions	Symbol	Value	Unit
Junction ambient	on glass fibre printed board (40 x 25 x 1.5) mm <sup>3</sup> plated with 35 $\mu\text{m}$ Cu	$R_{thJA}$	300	K/W

### Electrical DC Characteristics

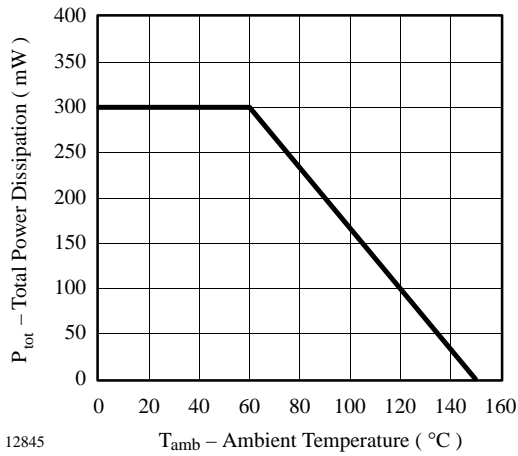
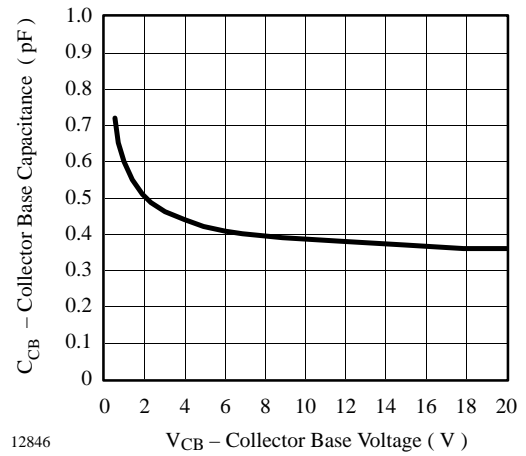
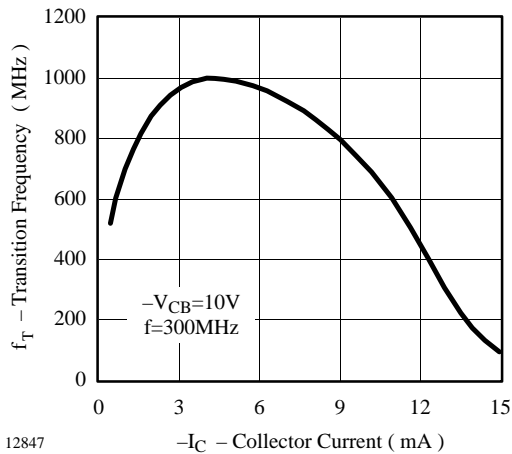
$T_{amb} = 25^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Collector cut-off current	$-V_{CE} = 40\text{ V}, V_{BE} = 0$	$-I_{CES}$			100	$\mu\text{A}$
Collector-base cut-off current	$-V_{CB} = 20\text{ V}, I_E = 0$	$-I_{CBO}$			100	nA
Emitter-base cut-off current	$-V_{EB} = 2\text{ V}, I_C = 0$	$-I_{EBO}$			10	$\mu\text{A}$
Collector-emitter breakdown voltage	$-I_C = 1\text{ mA}, I_B = 0$	$-V_{(BR)CEO}$	35			V
DC forward current transfer ratio	$-V_{CE} = 10\text{ V}, -I_C = 3\text{ mA}$	$h_{FE}$	25	50	90	

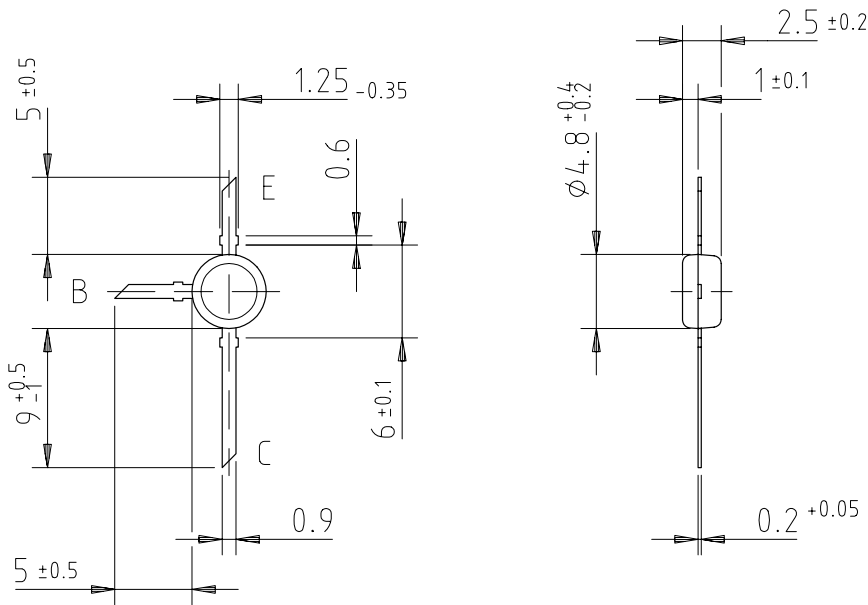
### Electrical AC Characteristics

$T_{amb} = 25^{\circ}\text{C}$ , unless otherwise specified

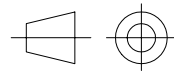
Parameter	Test Conditions	Sym- bol	Min	Typ	Max	Unit
Transition frequency	$-V_{CE} = 10\text{ V}, -I_C = 3\text{ mA}, f = 300\text{ MHz}$	$f_T$		1000		MHz
Collector-base capacitance	$-V_{CB} = 10\text{ V}, f = 1\text{ MHz}$	$C_{cb}$		0.4		pF
Noise figure	$-V_{CE} = 10\text{ V}, -I_C = 3\text{ mA}, Z_S = 50\ \Omega,$ $f = 800\text{ MHz}$	F		4.2	5.0	dB
Power gain	$-V_{CE} = 10\text{ V}, -I_C = 3\text{ mA}, Z_L = 500\ \Omega,$ $f = 800\text{ MHz}$	$G_{pb}$	13	14.5		dB
Collector current for $G_{pbmax}$	$-V_{CE} = 10\text{ V}, Z_L = 500\ \Omega, f = 800\text{ MHz}$	$-I_C$		5		mA

**Typical Characteristics** ( $T_{amb} = 25^{\circ}\text{C}$  unless otherwise specified)

**Figure 1. Total Power Dissipation vs. Ambient Temperature**

**Figure 3. Collector Base Capacitance vs. Collector Base Voltage**

**Figure 2. Transition Frequency vs. Collector Current**

### Dimensions of BF970 in mm



96 12243



technical drawings  
according to DIN  
specifications